



TO-92 Plastic-Encapsulate Transistors

2N6520 TRANSISTOR (PNP)

FEATURES

Power dissipation

$$P_{CM} : 0.625 \quad W \quad (T_{amb}=25^{\circ}C)$$

Collector current

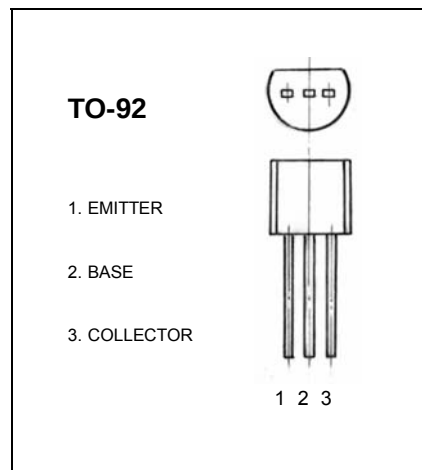
$$I_{CM} : -0.5 \quad A$$

Collector-base voltage

$$V_{(BR)CBO} : -350 \quad V$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^{\circ}C \quad \text{to} \quad +150^{\circ}C$$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100 \mu A, I_E = 0$	-350			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}^*$	$I_C = -1 \text{ mA}, I_B = 0$	-350			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10 \mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -250 \text{ V}, I_E = 0$			-0.05	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4 \text{ V}, I_C = 0$			-0.05	μA
DC current gain	h_{FE}	$V_{CE} = -10 \text{ V}, I_C = -1 \text{ mA}$ $V_{CE} = -10 \text{ V}, I_C = -10 \text{ mA}$ $V_{CE} = -10 \text{ V}, I_C = -30 \text{ mA}$ $V_{CE} = -10 \text{ V}, I_C = -50 \text{ mA}$ $V_{CE} = -10 \text{ V}, I_C = -100 \text{ mA}$	20 30 30 20 15		200 200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10 \text{ mA}, I_B = -1 \text{ mA}$ $I_C = -20 \text{ mA}, I_B = -2 \text{ mA}$ $I_C = -30 \text{ mA}, I_B = -3 \text{ mA}$ $I_C = -50 \text{ mA}, I_B = -5 \text{ mA}$			-0.3 -0.35 -0.5 -1	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -10 \text{ mA}, I_B = -1 \text{ mA}$ $I_C = -20 \text{ mA}, I_B = -2 \text{ mA}$ $I_C = -30 \text{ mA}, I_B = -3 \text{ mA}$			-0.75 -0.85 -0.9	V
Base-emitter voltage	$V_{BE(on)}$	$V_{CE} = -10 \text{ V}, I_C = -100 \text{ mA}$			-2	V
Transition frequency	f_T^*	$V_{CE} = -20 \text{ V}, I_C = -10 \text{ mA}$ $f = 20 \text{ MHz}$	40		200	MHz

* Pulse test, Pulse width $\leq 300 \mu s$, Duty cycle $\leq 2\%$.